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(71) Applicant (for all designated States except US): **GREAT WALL SEMICONDUCTOR CORPORATION** [US/US]; P.O. Box 24619, Southern Avenue, Tempe, AZ 85285-4619 (US).

(72) Inventor: **ANDERSON, Samuel**; 911 West Diamond Drive, Tempe, AZ 85283 (US).

(74) Agents: **SAMUEL, Richard, I.** et al.; Goodwin Procter LLP, 103 Eisenhower Parkway, Roseland, NJ 07068 (US).

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(57) Abstract: There is provided herein exemplary embodiments of a semiconductor device constructed in accordance with the present invention. The device comprises: a semiconductor chip having a lateral power transistor device formed therein. The chip has an upper surface and source, drain and gate contact terminals on the upper surface thereof. Each of the source, drain and gate contact terminals have a conductive ball or pillar bump thereon. A metal lead frame spans the upper surface of the chip, the metal lead frame being in electrical contact with the conductive balls or pillar bumps. A capsule encases the chip and at least a portion of the metal lead frame such that opposite ends of the metal lead from protrudes from opposite sides of the capsule.

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